

Welcome to [E-XFL.COM](https://www.e-xfl.com)

Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

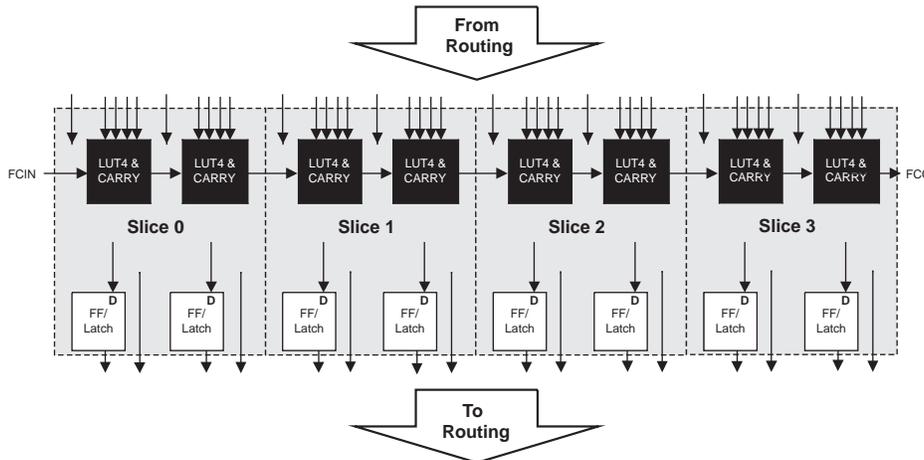
Details

Product Status	Active
Number of LABs/CLBs	1175
Number of Logic Elements/Cells	9400
Total RAM Bits	442368
Number of I/O	206
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LFBGA
Supplier Device Package	256-CABGA (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo3lf-9400e-5bg256c

PFU Blocks

The core of the MachXO3L/LF device consists of PFU blocks, which can be programmed to perform logic, arithmetic, distributed RAM and distributed ROM functions. Each PFU block consists of four interconnected slices numbered 0 to 3 as shown in Figure 2-3. Each slice contains two LUTs and two registers. There are 53 inputs and 25 outputs associated with each PFU block.

Figure 2-3. PFU Block Diagram



Slices

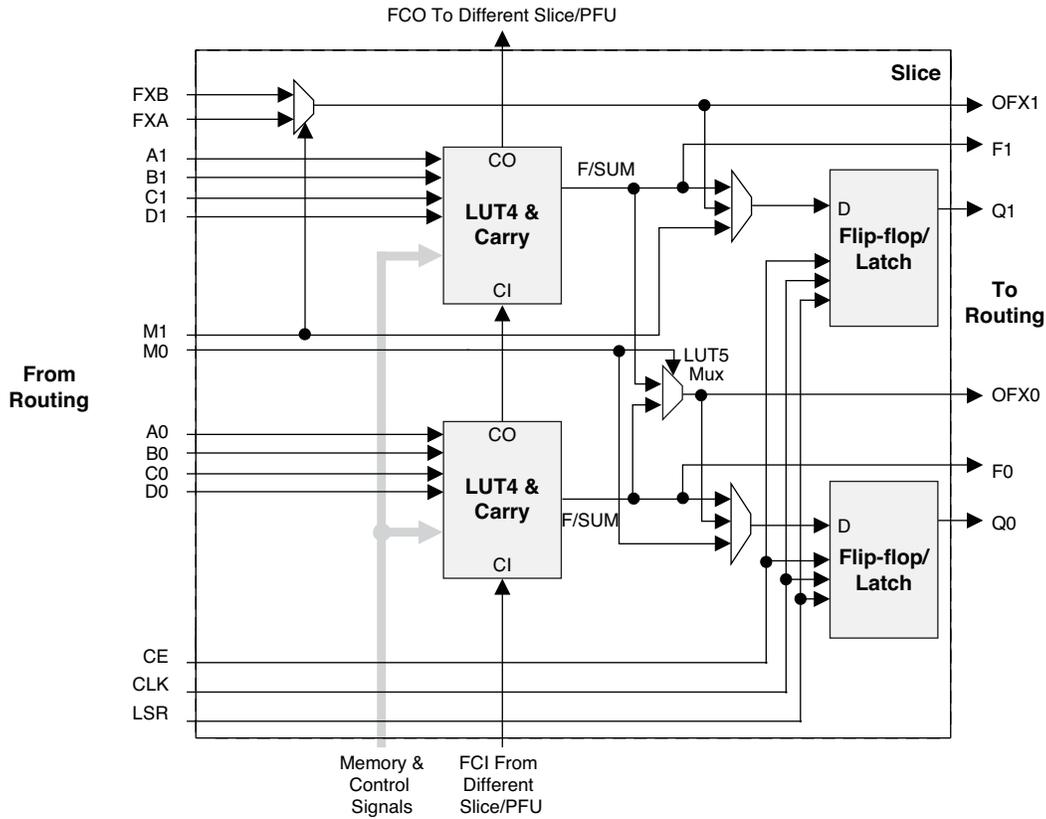
Slices 0-3 contain two LUT4s feeding two registers. Slices 0-2 can be configured as distributed memory. Table 2-1 shows the capability of the slices in PFU blocks along with the operation modes they enable. In addition, each PFU contains logic that allows the LUTs to be combined to perform functions such as LUT5, LUT6, LUT7 and LUT8. The control logic performs set/reset functions (programmable as synchronous/ asynchronous), clock select, chip-select and wider RAM/ROM functions.

Table 2-1. Resources and Modes Available per Slice

Slice	PFU Block	
	Resources	Modes
Slice 0	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM
Slice 1	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM
Slice 2	2 LUT4s and 2 Registers	Logic, Ripple, RAM, ROM
Slice 3	2 LUT4s and 2 Registers	Logic, Ripple, ROM

Figure 2-4 shows an overview of the internal logic of the slice. The registers in the slice can be configured for positive/negative and edge triggered or level sensitive clocks. All slices have 15 inputs from routing and one from the carry-chain (from the adjacent slice or PFU). There are seven outputs: six for routing and one to carry-chain (to the adjacent PFU). Table 2-2 lists the signals associated with Slices 0-3.

Figure 2-4. Slice Diagram



For Slices 0 and 1, memory control signals are generated from Slice 2 as follows:

- WCK is CLK
- WRE is from LSR
- DI[3:2] for Slice 1 and DI[1:0] for Slice 0 data from Slice 2
- WAD [A:D] is a 4-bit address from slice 2 LUT input

Table 2-2. Slice Signal Descriptions

Function	Type	Signal Names	Description
Input	Data signal	A0, B0, C0, D0	Inputs to LUT4
Input	Data signal	A1, B1, C1, D1	Inputs to LUT4
Input	Multi-purpose	M0/M1	Multi-purpose input
Input	Control signal	CE	Clock enable
Input	Control signal	LSR	Local set/reset
Input	Control signal	CLK	System clock
Input	Inter-PFU signal	FCIN	Fast carry in ¹
Output	Data signals	F0, F1	LUT4 output register bypass signals
Output	Data signals	Q0, Q1	Register outputs
Output	Data signals	OFX0	Output of a LUT5 MUX
Output	Data signals	OFX1	Output of a LUT6, LUT7, LUT8 ² MUX depending on the slice
Output	Inter-PFU signal	FCO	Fast carry out ¹

1. See Figure 2-3 for connection details.
2. Requires two PFUs.

Modes of Operation

Each slice has up to four potential modes of operation: Logic, Ripple, RAM and ROM.

Logic Mode

In this mode, the LUTs in each slice are configured as 4-input combinatorial lookup tables. A LUT4 can have 16 possible input combinations. Any four input logic functions can be generated by programming this lookup table. Since there are two LUT4s per slice, a LUT5 can be constructed within one slice. Larger look-up tables such as LUT6, LUT7 and LUT8 can be constructed by concatenating other slices. Note LUT8 requires more than four slices.

Ripple Mode

Ripple mode supports the efficient implementation of small arithmetic functions. In Ripple mode, the following functions can be implemented by each slice:

- Addition 2-bit
- Subtraction 2-bit
- Add/subtract 2-bit using dynamic control
- Up counter 2-bit
- Down counter 2-bit
- Up/down counter with asynchronous clear
- Up/down counter with preload (sync)
- Ripple mode multiplier building block
- Multiplier support
- Comparator functions of A and B inputs
 - A greater-than-or-equal-to B
 - A not-equal-to B
 - A less-than-or-equal-to B

Ripple mode includes an optional configuration that performs arithmetic using fast carry chain methods. In this configuration (also referred to as CCU2 mode) two additional signals, Carry Generate and Carry Propagate, are generated on a per-slice basis to allow fast arithmetic functions to be constructed by concatenating slices.

RAM Mode

In this mode, a 16x4-bit distributed single port RAM (SPR) can be constructed by using each LUT block in Slice 0 and Slice 1 as a 16x1-bit memory. Slice 2 is used to provide memory address and control signals.

MachXO3L/LF devices support distributed memory initialization.

The Lattice design tools support the creation of a variety of different size memories. Where appropriate, the software will construct these using distributed memory primitives that represent the capabilities of the PFU. Table 2-3 shows the number of slices required to implement different distributed RAM primitives. For more information about using RAM in MachXO3L/LF devices, please see TN1290, [Memory Usage Guide for MachXO3 Devices](#).

Table 2-3. Number of Slices Required For Implementing Distributed RAM

	SPR 16x4	PDPR 16x4
Number of slices	3	3

Note: SPR = Single Port RAM, PDPR = Pseudo Dual Port RAM

Table 2-6. EBR Signal Descriptions

Port Name	Description	Active State
CLK	Clock	Rising Clock Edge
CE	Clock Enable	Active High
OCE ¹	Output Clock Enable	Active High
RST	Reset	Active High
BE ¹	Byte Enable	Active High
WE	Write Enable	Active High
AD	Address Bus	—
DI	Data In	—
DO	Data Out	—
CS	Chip Select	Active High
AFF	FIFO RAM Almost Full Flag	—
FF	FIFO RAM Full Flag	—
AEF	FIFO RAM Almost Empty Flag	—
EF	FIFO RAM Empty Flag	—
RPRST	FIFO RAM Read Pointer Reset	—

1. Optional signals.
2. For dual port EBR primitives a trailing 'A' or 'B' in the signal name specifies the EBR port A or port B respectively.
3. For FIFO RAM mode primitive, a trailing 'R' or 'W' in the signal name specifies the FIFO read port or write port respectively.
4. For FIFO RAM mode primitive FULLI has the same function as CSW(2) and EMPTYI has the same function as CSR(2).
5. In FIFO mode, CLKW is the write port clock, CSW is the write port chip select, CLKR is the read port clock, CSR is the read port chip select, ORE is the output read enable.

The EBR memory supports three forms of write behavior for single or dual port operation:

1. **Normal** – Data on the output appears only during the read cycle. During a write cycle, the data (at the current address) does not appear on the output. This mode is supported for all data widths.
2. **Write Through** – A copy of the input data appears at the output of the same port. This mode is supported for all data widths.
3. **Read-Before-Write** – When new data is being written, the old contents of the address appears at the output.

FIFO Configuration

The FIFO has a write port with data-in, CEW, WE and CLKW signals. There is a separate read port with data-out, RCE, RE and CLKR signals. The FIFO internally generates Almost Full, Full, Almost Empty and Empty Flags. The Full and Almost Full flags are registered with CLKW. The Empty and Almost Empty flags are registered with CLKR. Table 2-7 shows the range of programming values for these flags.

Table 2-7. Programmable FIFO Flag Ranges

Flag Name	Programming Range
Full (FF)	1 to max (up to 2^N-1)
Almost Full (AF)	1 to Full-1
Almost Empty (AE)	1 to Full-1
Empty (EF)	0

N = Address bit width.

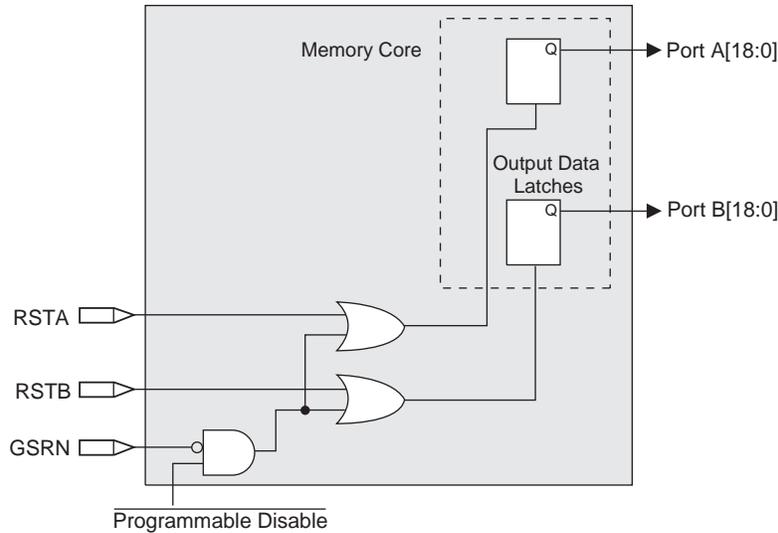
The FIFO state machine supports two types of reset signals: RST and RPRST. The RST signal is a global reset that clears the contents of the FIFO by resetting the read/write pointer and puts the FIFO flags in their initial reset

state. The RPRST signal is used to reset the read pointer. The purpose of this reset is to retransmit the data that is in the FIFO. In these applications it is important to keep careful track of when a packet is written into or read from the FIFO.

Memory Core Reset

The memory core contains data output latches for ports A and B. These are simple latches that can be reset synchronously or asynchronously. RSTA and RSTB are local signals, which reset the output latches associated with port A and port B respectively. The Global Reset (GSRN) signal resets both ports. The output data latches and associated resets for both ports are as shown in Figure 2-9.

Figure 2-9. Memory Core Reset

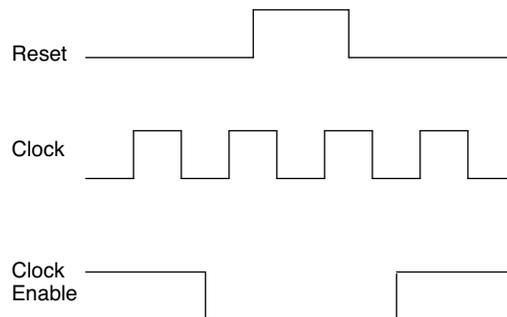


For further information on the sysMEM EBR block, please refer to TN1290, [Memory Usage Guide for MachXO3 Devices](#).

EBR Asynchronous Reset

EBR asynchronous reset or GSR (if used) can only be applied if all clock enables are low for a clock cycle before the reset is applied and released a clock cycle after the reset is released, as shown in Figure 2-10. The GSR input to the EBR is always asynchronous.

Figure 2-10. EBR Asynchronous Reset (Including GSR) Timing Diagram



If all clock enables remain enabled, the EBR asynchronous reset or GSR may only be applied and released after the EBR read and write clock inputs are in a steady state condition for a minimum of $1/f_{MAX}$ (EBR clock). The reset release must adhere to the EBR synchronous reset setup time before the next active read or write clock edge.

Input Gearbox

Each PIC on the bottom edge has a built-in 1:8 input gearbox. Each of these input gearboxes may be programmed as a 1:7 de-serializer or as one IDDRX4 (1:8) gearbox or as two IDDRX2 (1:4) gearboxes. Table 2-9 shows the gearbox signals.

Table 2-9. Input Gearbox Signal List

Name	I/O Type	Description
D	Input	High-speed data input after programmable delay in PIO A input register block
ALIGNWD	Input	Data alignment signal from device core
SCLK	Input	Slow-speed system clock
ECLK[1:0]	Input	High-speed edge clock
RST	Input	Reset
Q[7:0]	Output	Low-speed data to device core: Video RX(1:7): Q[6:0] GDDR4(1:8): Q[7:0] GDDR2(1:4)(IOL-A): Q4, Q5, Q6, Q7 GDDR2(1:4)(IOL-C): Q0, Q1, Q2, Q3

These gearboxes have three stage pipeline registers. The first stage registers sample the high-speed input data by the high-speed edge clock on its rising and falling edges. The second stage registers perform data alignment based on the control signals UPDATE and SEL0 from the control block. The third stage pipeline registers pass the data to the device core synchronized to the low-speed system clock. Figure 2-13 shows a block diagram of the input gearbox.

Output Gearbox

Each PIC on the top edge has a built-in 8:1 output gearbox. Each of these output gearboxes may be programmed as a 7:1 serializer or as one ODDR4 (8:1) gearbox or as two ODDR2 (4:1) gearboxes. Table 2-10 shows the gearbox signals.

Table 2-10. Output Gearbox Signal List

Name	I/O Type	Description
Q	Output	High-speed data output
D[7:0]	Input	Low-speed data from device core
Video TX(7:1): D[6:0]		
GDDR4(8:1): D[7:0]		
GDDR2(4:1)(IOL-A): D[3:0]		
GDDR2(4:1)(IOL-C): D[7:4]		
SCLK	Input	Slow-speed system clock
ECLK [1:0]	Input	High-speed edge clock
RST	Input	Reset

The gearboxes have three stage pipeline registers. The first stage registers sample the low-speed input data on the low-speed system clock. The second stage registers transfer data from the low-speed clock registers to the high-speed clock registers. The third stage pipeline registers controlled by high-speed edge clock shift and mux the high-speed data out to the sysIO buffer. Figure 2-14 shows the output gearbox block diagram.

Table 2-11 shows the I/O standards (together with their supply and reference voltages) supported by the MachXO3L/LF devices. For further information on utilizing the sysIO buffer to support a variety of standards please see TN1280, [MachXO3 sysIO Usage Guide](#).

Table 2-11. Supported Input Standards

Input Standard	VCCIO (Typ.)				
	3.3 V	2.5 V	1.8 V	1.5 V	1.2 V
Single-Ended Interfaces					
LVTTTL	Yes				
LVC MOS33	Yes				
LVC MOS25		Yes			
LVC MOS18			Yes		
LVC MOS15				Yes	
LVC MOS12					Yes
PCI	Yes				
Differential Interfaces					
LVDS	Yes	Yes			
BLVDS, MLVDS, LVPECL, RSDS	Yes	Yes			
MIPI ¹	Yes	Yes			
LVTTLD	Yes				
LVC MOS33D	Yes				
LVC MOS25D		Yes			
LVC MOS18D			Yes		

1. These interfaces can be emulated with external resistors in all devices.

Table 2-12. Supported Output Standards

Output Standard	V _{CCIO} (Typ.)
Single-Ended Interfaces	
LVTTTL	3.3
LVC MOS33	3.3
LVC MOS25	2.5
LVC MOS18	1.8
LVC MOS15	1.5
LVC MOS12	1.2
LVC MOS33, Open Drain	—
LVC MOS25, Open Drain	—
LVC MOS18, Open Drain	—
LVC MOS15, Open Drain	—
LVC MOS12, Open Drain	—
PCI33	3.3
Differential Interfaces	
LVDS ¹	2.5, 3.3
BLVDS, MLVDS, RSDS ¹	2.5
LVPECL ¹	3.3
MIPI ¹	2.5
LVTTLD	3.3
LVC MOS33D	3.3
LVC MOS25D	2.5
LVC MOS18D	1.8

1. These interfaces can be emulated with external resistors in all devices.

sysIO Buffer Banks

The numbers of banks vary between the devices of this family. MachXO3L/LF-1300 in the 256 Ball packages and the MachXO3L/LF-2100 and higher density devices have six I/O banks (one bank on the top, right and bottom side and three banks on the left side). The MachXO3L/LF-1300 and lower density devices have four banks (one bank per side). Figures 2-15 and 2-16 show the sysIO banks and their associated supplies for all devices.

Figure 2-15. MachXO3L/LF-1300 in 256 Ball Packages, MachXO3L/LF-2100, MachXO3L/LF-4300, MachXO3L/LF-6900 and MachXO3L/LF-9400 Banks

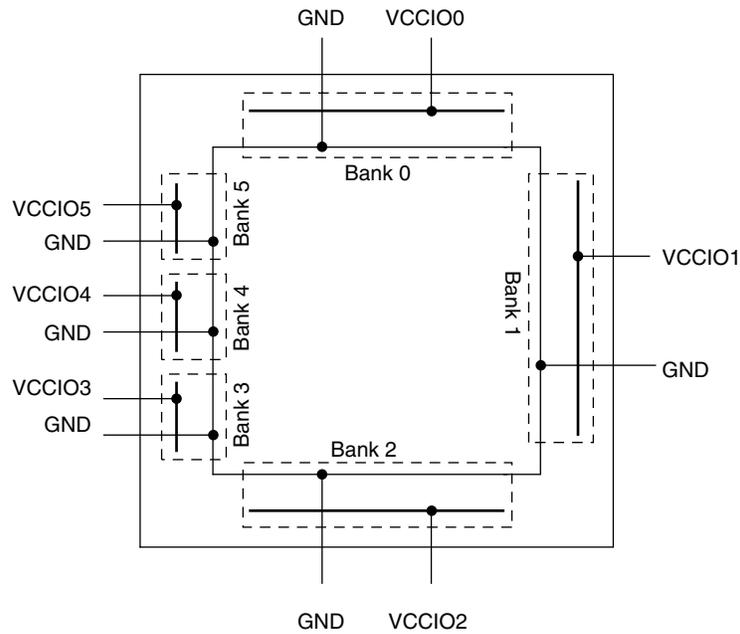


Figure 2-16. MachXO3L/LF-640 and MachXO3L/LF-1300 Banks

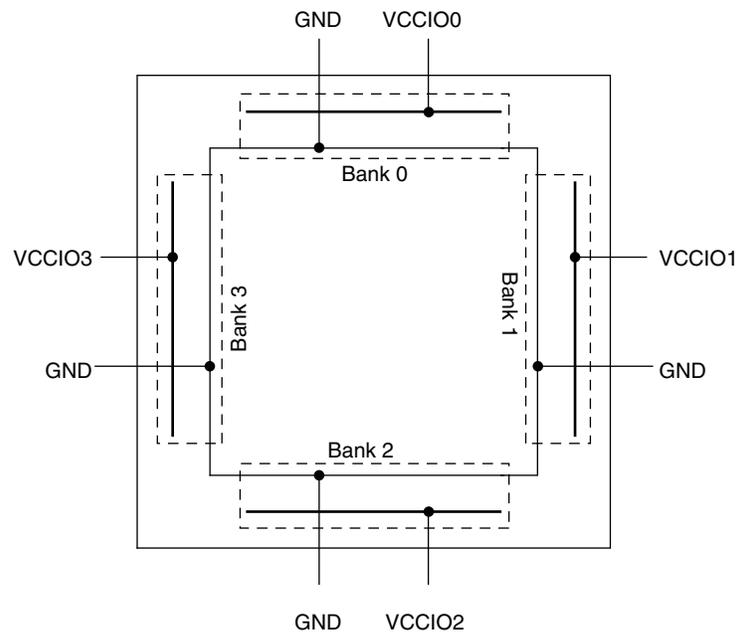


Table 2-17. MachXO3L/LF Power Saving Features Description

Device Subsystem	Feature Description
Bandgap	The bandgap can be turned off in standby mode. When the Bandgap is turned off, analog circuitry such as the POR, PLLs, on-chip oscillator, and differential I/O buffers are also turned off. Bandgap can only be turned off for 1.2 V devices.
Power-On-Reset (POR)	The POR can be turned off in standby mode. This monitors V _{CC} levels. In the event of unsafe V _{CC} drops, this circuit reconfigures the device. When the POR circuitry is turned off, limited power detector circuitry is still active. This option is only recommended for applications in which the power supply rails are reliable.
On-Chip Oscillator	The on-chip oscillator has two power saving features. It may be switched off if it is not needed in your design. It can also be turned off in Standby mode.
PLL	Similar to the on-chip oscillator, the PLL also has two power saving features. It can be statically switched off if it is not needed in a design. It can also be turned off in Standby mode. The PLL will wait until all output clocks from the PLL are driven low before powering off.
I/O Bank Controller	Differential I/O buffers (used to implement standards such as LVDS) consume more than ratioed single-ended I/Os such as LVCMOS and LVTTL. The I/O bank controller allows the user to turn these I/Os off dynamically on a per bank selection.
Dynamic Clock Enable for Primary Clock Nets	Each primary clock net can be dynamically disabled to save power.
Power Guard	Power Guard is a feature implemented in input buffers. This feature allows users to switch off the input buffer when it is not needed. This feature can be used in both clock and data paths. Its biggest impact is that in the standby mode it can be used to switch off clock inputs that are distributed using general routing resources.

For more details on the standby mode refer to TN1289, [Power Estimation and Management for MachXO3 Devices](#).

Power On Reset

MachXO3L/LF devices have power-on reset circuitry to monitor V_{CCINT} and V_{CCIO} voltage levels during power-up and operation. At power-up, the POR circuitry monitors V_{CCINT} and V_{CCIO0} (controls configuration) voltage levels. It then triggers download from the on-chip configuration NVCM/Flash memory after reaching the V_{PORUP} level specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet. For “E” devices without voltage regulators, V_{CCINT} is the same as the V_{CC} supply voltage. For “C” devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage. From this voltage reference, the time taken for configuration and entry into user mode is specified as NVCM/Flash Download Time (t_{REFRESH}) in the DC and Switching Characteristics section of this data sheet. Before and during configuration, the I/Os are held in tri-state. I/Os are released to user functionality once the device has finished configuration. Note that for “C” devices, a separate POR circuit monitors external V_{CC} voltage in addition to the POR circuit that monitors the internal post-regulated power supply voltage level.

Once the device enters into user mode, the POR circuitry can optionally continue to monitor V_{CCINT} levels. If V_{CCINT} drops below V_{PORDNBG} level (with the bandgap circuitry switched on) or below V_{PORDNSRAM} level (with the bandgap circuitry switched off to conserve power) device functionality cannot be guaranteed. In such a situation the POR issues a reset and begins monitoring the V_{CCINT} and V_{CCIO} voltage levels. V_{PORDNBG} and V_{PORDNSRAM} are both specified in the Power-On-Reset Voltage table in the DC and Switching Characteristics section of this data sheet.

Note that once an “E” device enters user mode, users can switch off the bandgap to conserve power. When the bandgap circuitry is switched off, the POR circuitry also shuts down. The device is designed such that a mini-mal, low power POR circuit is still operational (this corresponds to the V_{PORDNSRAM} reset point described in the paragraph above). However this circuit is not as accurate as the one that operates when the bandgap is switched on. The low power POR circuit emulates an SRAM cell and is biased to trip before the vast majority of SRAM cells flip. If users are concerned about the V_{CC} supply dropping below V_{CC} (min) they should not shut down the bandgap or POR circuit.

TraceID

Each MachXO3L/LF device contains a unique (per device), TraceID that can be used for tracking purposes or for IP security applications. The TraceID is 64 bits long. Eight out of 64 bits are user-programmable, the remaining 56 bits are factory-programmed. The TraceID is accessible through the EFB WISHBONE interface and can also be accessed through the SPI, I²C, or JTAG interfaces.

Density Shifting

The MachXO3L/LF family has been designed to enable density migration within the same package. Furthermore, the architecture ensures a high success rate when performing design migration from lower density devices to higher density devices. In many cases, it is also possible to shift a lower utilization design targeted for a high-density device to a lower density device. However, the exact details of the final resource utilization will impact the likely success in each case. When migrating from lower to higher density or higher to lower density, ensure to review all the power supplies and NC pins of the chosen devices. For more details refer to the [MachXO3 migration files](#).

sysIO Single-Ended DC Electrical Characteristics^{1, 2}

Input/Output Standard	V _{IL}		V _{IH}		V _{OL} Max. (V)	V _{OH} Min. (V)	I _{OL} Max. ⁴ (mA)	I _{OH} Max. ⁴ (mA)
	Min. (V) ³	Max. (V)	Min. (V)	Max. (V)				
LVCMOS 3.3 LVTTTL	-0.3	0.8	2.0	3.6	0.4	V _{CCIO} - 0.4	4	-4
							8	-8
					12		-12	
					16		-16	
					0.2	V _{CCIO} - 0.2	0.1	-0.1
LVCMOS 2.5	-0.3	0.7	1.7	3.6	0.4	V _{CCIO} - 0.4	4	-4
							8	-8
					12		-12	
					16		-16	
					0.2	V _{CCIO} - 0.2	0.1	-0.1
LVCMOS 1.8	-0.3	0.35V _{CCIO}	0.65V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	4	-4
							8	-8
					12		-12	
					16		-16	
					0.2	V _{CCIO} - 0.2	0.1	-0.1
LVCMOS 1.5	-0.3	0.35V _{CCIO}	0.65V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	4	-4
					0.2		V _{CCIO} - 0.2	0.1
LVCMOS 1.2	-0.3	0.35V _{CCIO}	0.65V _{CCIO}	3.6	0.4	V _{CCIO} - 0.4	4	-2
					0.2		V _{CCIO} - 0.2	0.1
LVCMOS25R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS18R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS18R25	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS15R33	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS15R25	-0.3	VREF-0.1	VREF+0.1	3.6	NA	NA	NA	NA
LVCMOS12R33	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS10R25	-0.3	VREF-0.1	VREF+0.1	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain

1. MachXO3L/LF devices allow LVCMOS inputs to be placed in I/O banks where V_{CCIO} is different from what is specified in the applicable JEDEC specification. This is referred to as a ratioed input buffer. In a majority of cases this operation follows or exceeds the applicable JEDEC specification. The cases where MachXO3L/LF devices do not meet the relevant JEDEC specification are documented in the table below.
2. MachXO3L/LF devices allow for LVCMOS referenced I/Os which follow applicable JEDEC specifications. For more details about mixed mode operation please refer to please refer to TN1280, [MachXO3 sysIO Usage Guide](#).
3. The dual function I²C pins SCL and SDA are limited to a V_{IL} min of -0.25 V or to -0.3 V with a duration of <10 ns.
4. For electromigration, the average DC current sourced or sinked by I/O pads between two consecutive V_{CCIO} or GND pad connections, or between the last V_{CCIO} or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed a maximum of n * 8 mA. "n" is the number of I/O pads between the two consecutive bank V_{CCIO} or GND connections or between the last V_{CCIO} and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

sysIO Differential Electrical Characteristics

The LVDS differential output buffers are available on the top side of the MachXO3L/LF PLD family.

LVDS

Over Recommended Operating Conditions

Parameter Symbol	Parameter Description	Test Conditions	Min.	Typ.	Max.	Units
V _{INP} V _{INM}	Input Voltage	V _{CCIO} = 3.3 V	0	—	2.605	V
		V _{CCIO} = 2.5 V	0	—	2.05	V
V _{THD}	Differential Input Threshold		±100	—		mV
V _{CM}	Input Common Mode Voltage	V _{CCIO} = 3.3 V	0.05	—	2.6	V
		V _{CCIO} = 2.5 V	0.05	—	2.0	V
I _{IN}	Input current	Power on	—	—	±10	μA
V _{OH}	Output high voltage for V _{OP} or V _{OM}	R _T = 100 Ohm	—	1.375	—	V
V _{OL}	Output low voltage for V _{OP} or V _{OM}	R _T = 100 Ohm	0.90	1.025	—	V
V _{OD}	Output voltage differential	(V _{OP} - V _{OM}), R _T = 100 Ohm	250	350	450	mV
ΔV _{OD}	Change in V _{OD} between high and low		—	—	50	mV
V _{OS}	Output voltage offset	(V _{OP} - V _{OM})/2, R _T = 100 Ohm	1.125	1.20	1.395	V
ΔV _{OS}	Change in V _{OS} between H and L		—	—	50	mV
I _{OSD}	Output short circuit current	V _{OD} = 0 V driver outputs shorted	—	—	24	mA

Parameter	Description	Device	-6		-5		Units
			Min.	Max.	Min.	Max.	
Generic DDRX4 Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input – GDDR4_TX.ECLK.Centered^{8,9}							
t _{DVB}	Output Data Valid Before CLK Output	MachXO3L/LF devices, top side only	0.455	—	0.570	—	ns
t _{DVA}	Output Data Valid After CLK Output		0.455	—	0.570	—	ns
f _{DATA}	DDR4 Serial Output Data Speed		—	800	—	630	Mbps
f _{DDR4}	DDR4 ECLK Frequency (minimum limited by PLL)		—	400	—	315	MHz
f _{SCLK}	SCLK Frequency		—	100	—	79	MHz
7:1 LVDS Outputs – GDDR71_TX.ECLK.7:1^{8,9}							
t _{DIB}	Output Data Invalid Before CLK Output	MachXO3L/LF devices, top side only	—	0.160	—	0.180	ns
t _{DIA}	Output Data Invalid After CLK Output		—	0.160	—	0.180	ns
f _{DATA}	DDR71 Serial Output Data Speed		—	756	—	630	Mbps
f _{DDR71}	DDR71 ECLK Frequency		—	378	—	315	MHz
f _{CLKOUT}	7:1 Output Clock Frequency (SCLK) (minimum limited by PLL)		—	108	—	90	MHz
MIPI D-PHY Outputs with Clock and Data Centered at Pin Using PCLK Pin for Clock Input - GDDR4_TX.ECLK.Centered^{10,11,12}							
t _{DVB}	Output Data Valid Before CLK Output	All MachXO3L/LF devices, top side only	0.200	—	0.200	—	UI
t _{DVA}	Output Data Valid After CLK Output		0.200	—	0.200	—	UI
f _{DATA} ¹⁴	MIPI D-PHY Output Data Speed		—	900	—	900	Mbps
f _{DDR4} ¹⁴	MIPI D-PHY ECLK Frequency (minimum limited by PLL)		—	450	—	450	MHz
f _{SCLK} ¹⁴	SCLK Frequency		—	112.5	—	112.5	MHz

1. Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
2. General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0pF load, fast slew rate.
3. Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
4. 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
5. For Generic DDRX1 mode t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03 ns)/2.
6. The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 105 ps (-6), 113 ps (-5), 120 ps (-4).
7. This number for general purpose usage. Duty cycle tolerance is +/-10%.
8. Duty cycle is +/- 5% for system usage.
9. Performance is calculated with 0.225 UI.
10. Performance is calculated with 0.20 UI.
11. Performance for Industrial devices are only supported with VCC between 1.16 V to 1.24 V.
12. Performance for Industrial devices and -5 devices are not modeled in the Diamond design tool.
13. The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
14. Above 800 Mbps is only supported with WLCSP and csfBGA packages
15. Between 800 Mbps to 900 Mbps:
 - a. VIDTH exceeds the MIPI D-PHY Input DC Conditions Table 3-4 and can be calculated with the equation t_{SU} or t_H = -0.0005*VIDTH + 0.3284
 - b. Example calculations
 - i. t_{SU} and t_{HO} = 0.28 with VIDTH = 100 mV
 - ii. t_{SU} and t_{HO} = 0.25 with VIDTH = 170 mV
 - iii. t_{SU} and t_{HO} = 0.20 with VIDTH = 270 mV

Figure 3-6. Receiver GDDR71_RX. Waveforms

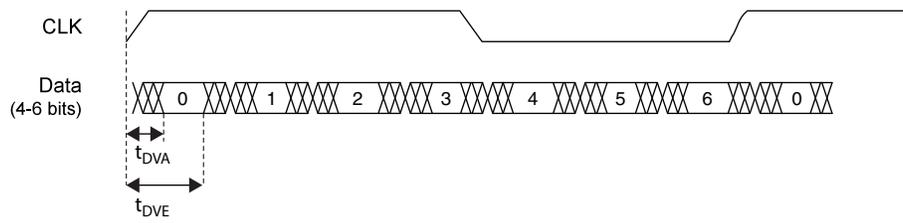
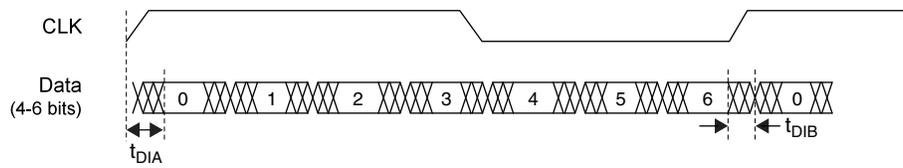


Figure 3-7. Transmitter GDDR71_TX. Waveforms



	MachXO3L/LF-4300						
	WLCSP81	CSFBGA121	CSFBGA256	CSFBGA324	CABGA256	CABGA324	CABGA400
General Purpose IO per Bank							
Bank 0	29	24	50	71	50	71	83
Bank 1	0	26	52	62	52	68	84
Bank 2	20	26	52	72	52	72	84
Bank 3	7	7	16	22	16	24	28
Bank 4	0	7	16	14	16	16	24
Bank 5	7	10	20	27	20	28	32
Total General Purpose Single Ended IO	63	100	206	268	206	279	335
Differential IO per Bank							
Bank 0	15	12	25	36	25	36	42
Bank 1	0	13	26	30	26	34	42
Bank 2	10	13	26	36	26	36	42
Bank 3	3	3	8	10	8	12	14
Bank 4	0	3	8	6	8	8	12
Bank 5	3	5	10	13	10	14	16
Total General Purpose Differential IO	31	49	103	131	103	140	168
Dual Function IO	25	37	37	37	37	37	37
Number 7:1 or 8:1 Gearboxes							
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	10	7	18	18	18	18	21
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	10	13	18	18	18	18	21
High-speed Differential Outputs							
Bank 0	10	7	18	18	18	18	21
VCCIO Pins							
Bank 0	3	1	4	4	4	4	5
Bank 1	0	1	3	4	4	4	5
Bank 2	2	1	4	4	4	4	5
Bank 3	1	1	2	2	1	2	2
Bank 4	0	1	2	2	2	2	2
Bank 5	1	1	2	2	1	2	2
VCC	4	4	8	8	8	10	10
GND	6	10	24	16	24	16	33
NC	0	0	0	13	1	0	0
Reserved for Configuration	1	1	1	1	1	1	1
Total Count of Bonded Pins	81	121	256	324	256	324	400

	MachXO3L/LF-6900				
	CSFBGA256	CSFBGA324	CABGA256	CABGA324	CABGA400
General Purpose IO per Bank					
Bank 0	50	73	50	71	83
Bank 1	52	68	52	68	84
Bank 2	52	72	52	72	84
Bank 3	16	24	16	24	28
Bank 4	16	16	16	16	24
Bank 5	20	28	20	28	32
Total General Purpose Single Ended IO	206	281	206	279	335
Differential IO per Bank					
Bank 0	25	36	25	36	42
Bank 1	26	34	26	34	42
Bank 2	26	36	26	36	42
Bank 3	8	12	8	12	14
Bank 4	8	8	8	8	12
Bank 5	10	14	10	14	16
Total General Purpose Differential IO	103	140	103	140	168
Dual Function IO	37	37	37	37	37
Number 7:1 or 8:1 Gearboxes					
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	20	21	20	21	21
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	20	21	20	21	21
High-speed Differential Outputs					
Bank 0	20	21	20	21	21
VCCIO Pins					
Bank 0	4	4	4	4	5
Bank 1	3	4	4	4	5
Bank 2	4	4	4	4	5
Bank 3	2	2	1	2	2
Bank 4	2	2	2	2	2
Bank 5	2	2	1	2	2
VCC	8	8	8	10	10
GND	24	16	24	16	33
NC	0	0	1	0	0
Reserved for Configuration	1	1	1	1	1
Total Count of Bonded Pins	256	324	256	324	400

	MachXO3L/LF-9400C			
	CSFBGA256	CABGA256	CABGA400	CABGA484
General Purpose IO per Bank				
Bank 0	50	50	83	95
Bank 1	52	52	84	96
Bank 2	52	52	84	96
Bank 3	16	16	28	36
Bank 4	16	16	24	24
Bank 5	20	20	32	36
Total General Purpose Single Ended IO	206	206	335	383
Differential IO per Bank				
Bank 0	25	25	42	48
Bank 1	26	26	42	48
Bank 2	26	26	42	48
Bank 3	8	8	14	18
Bank 4	8	8	12	12
Bank 5	10	10	16	18
Total General Purpose Differential IO	103	103	168	192
Dual Function IO	37	37	37	45
Number 7:1 or 8:1 Gearboxes				
Number of 7:1 or 8:1 Output Gearbox Available (Bank 0)	20	20	22	24
Number of 7:1 or 8:1 Input Gearbox Available (Bank 2)	20	20	22	24
High-speed Differential Outputs				
Bank 0	20	20	21	24
VCCIO Pins				
Bank 0	4	4	5	9
Bank 1	3	4	5	9
Bank 2	4	4	5	9
Bank 3	2	1	2	3
Bank 4	2	2	2	3
Bank 5	2	1	2	3
VCC	8	8	10	12
GND	24	24	33	52
NC	0	1	0	0
Reserved for Configuration	1	1	1	1
Total Count of Bonded Pins	256	256	400	484

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-6900E-5MG256C	6900	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3L-6900E-6MG256C	6900	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3L-6900E-5MG256I	6900	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3L-6900E-6MG256I	6900	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3L-6900E-5MG324C	6900	1.2 V	5	Halogen-Free csfBGA	324	COM
LCMXO3L-6900E-6MG324C	6900	1.2 V	6	Halogen-Free csfBGA	324	COM
LCMXO3L-6900E-5MG324I	6900	1.2 V	5	Halogen-Free csfBGA	324	IND
LCMXO3L-6900E-6MG324I	6900	1.2 V	6	Halogen-Free csfBGA	324	IND
LCMXO3L-6900C-5BG256C	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3L-6900C-6BG256C	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3L-6900C-5BG256I	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3L-6900C-6BG256I	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3L-6900C-5BG324C	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	COM
LCMXO3L-6900C-6BG324C	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	COM
LCMXO3L-6900C-5BG324I	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	324	IND
LCMXO3L-6900C-6BG324I	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	324	IND
LCMXO3L-6900C-5BG400C	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	COM
LCMXO3L-6900C-6BG400C	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	COM
LCMXO3L-6900C-5BG400I	6900	2.5 V / 3.3 V	5	Halogen-Free caBGA	400	IND
LCMXO3L-6900C-6BG400I	6900	2.5 V / 3.3 V	6	Halogen-Free caBGA	400	IND

Part Number	LUTs	Supply Voltage	Speed	Package	Leads	Temp.
LCMXO3L-9400E-5MG256C	9400	1.2 V	5	Halogen-Free csfBGA	256	COM
LCMXO3L-9400E-6MG256C	9400	1.2 V	6	Halogen-Free csfBGA	256	COM
LCMXO3L-9400E-5MG256I	9400	1.2 V	5	Halogen-Free csfBGA	256	IND
LCMXO3L-9400E-6MG256I	9400	1.2 V	6	Halogen-Free csfBGA	256	IND
LCMXO3L-9400C-5BG256C	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	256	COM
LCMXO3L-9400C-6BG256C	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	256	COM
LCMXO3L-9400C-5BG256I	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	256	IND
LCMXO3L-9400C-6BG256I	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	256	IND
LCMXO3L-9400C-5BG400C	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	400	COM
LCMXO3L-9400C-6BG400C	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	400	COM
LCMXO3L-9400C-5BG400I	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	400	IND
LCMXO3L-9400C-6BG400I	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	400	IND
LCMXO3L-9400C-5BG484C	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	484	COM
LCMXO3L-9400C-6BG484C	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	484	COM
LCMXO3L-9400C-5BG484I	9400	2.5 V/3.3 V	5	Halogen-Free caBGA	484	IND
LCMXO3L-9400C-6BG484I	9400	2.5 V/3.3 V	6	Halogen-Free caBGA	484	IND